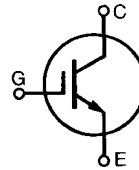


HiPerFAST™ IGBT Lightspeed™ Series

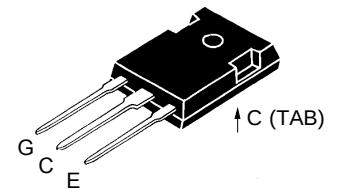
IXGH 12N90C
IXGX 12N90C

$$\begin{aligned} V_{CES} &= 900 \text{ V} \\ I_{C25} &= 24 \text{ A} \\ V_{CES(sat)} &= 3.0 \text{ V} \\ t_{fi(typ)} &= 70 \text{ ns} \end{aligned}$$

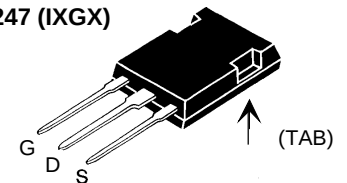


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	900	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	900	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	24	A
I_{C90}	$T_C = 90^\circ\text{C}$	12	A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	48	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 33 \Omega$ Clamped inductive load	$I_{CM} = 24$ @ $0.8 V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	100	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque with screw M3 Mounting torque with screw M3.5	0.45/4 Nm/lb.in. 0.55/5 Nm/lb.in.	
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
Weight		6	g

TO-247 (IXGH)



PLUS 247 (IXGX)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- Very high frequency IGBT
- New generation HDMOS™ process
- International standard package
- High peak current handling capability

Applications

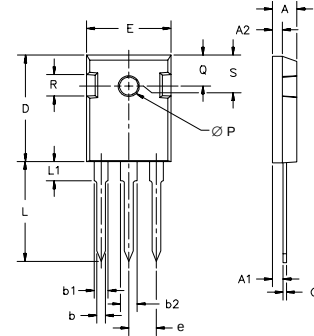
- PFC circuit
- AC motor speed control
- DC servo and robot drives
- Switch-mode and resonant-mode power supplies
- High power audio amplifiers

Advantages

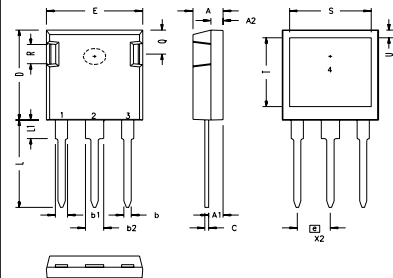
- Fast switching speed
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250 \mu\text{A}, V_{GE} = 0 \text{ V}$	900		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{GE} = V_{GE}$	2.5		5.0 V
I_{CES}	$V_{CE} = V_{CES}$ $V_{GE} = 0 \text{ V}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			100 μA 1.5 mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{CE90}, V_{GE} = 15 \text{ V}$			3.0 V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}, V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$	5	10	S
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		780	pF
C_{oes}			60	pF
C_{res}			15	pF
Q_g	$I_C = I_{C90}, V_{GE} = 15\text{ V}, V_{CE} = 0.5 V_{CES}$		33	nC
Q_{ge}			10	nC
Q_{gc}			12	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}$ $V_{CE} = 0.8 \cdot V_{CES}, R_G = R_{off} = 22\text{ }\Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		20	ns
t_{ri}			20	ns
$t_{d(off)}$		135	200	ns
t_{fi}		70	180	ns
E_{off}		0.32	0.70	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}$ $V_{CE} = 0.8 \cdot V_{CES}, R_G = R_{off} = 22\text{ }\Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		20	ns
t_{ri}			20	ns
E_{on}		0.15		mJ
$t_{d(off)}$		200		ns
t_{fi}		150		ns
E_{off}		0.70		mJ
R_{thJC}				1.25 K/W
R_{thCK}	TO-247	0.25		K/W
	PLUS 247	0.15		K/W

TO-247 Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

PLUS 247 Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03

- 1 - GATE
 2 - DRAIN (COLLECTOR)
 3 - SOURCE (EMITTER)
 4 - NO CONNECTION

NOTE: This drawing will meet all dimensions
 requirement of JEDEC outline TO-247AD
 except screw hole.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more
 of the following U.S. patents:

4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1
 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343

Fig. 1. Saturation Voltage Characteristics @ 25°C

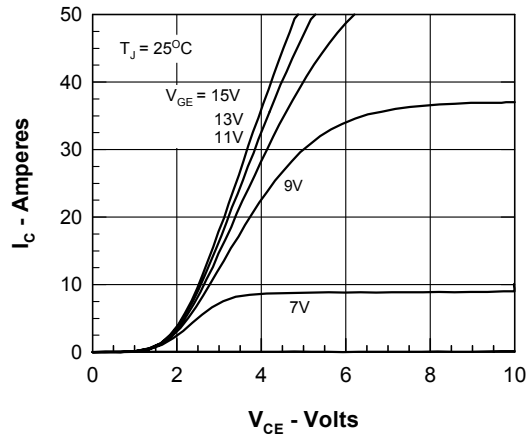


Fig. 2. Extended Output Characteristics

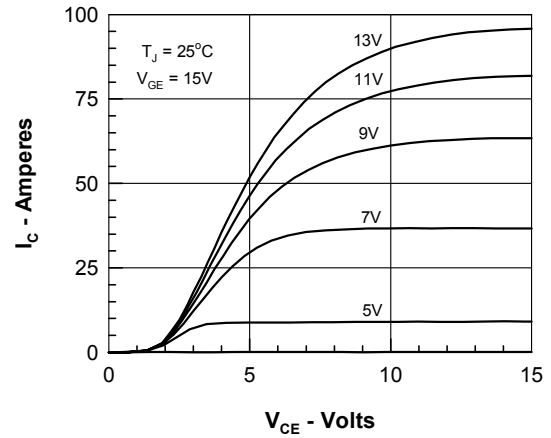


Fig. 3. Saturation Voltage Characteristics @ 125°C

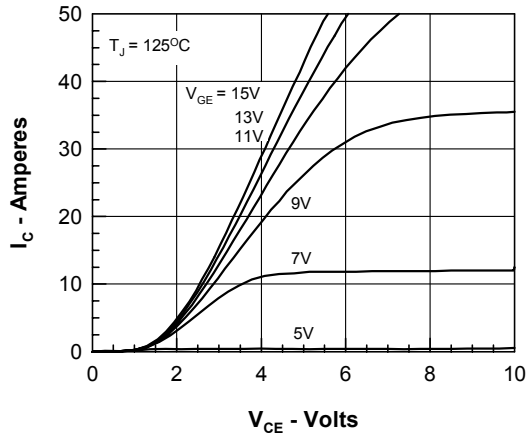


Fig. 4. Temperature Dependence of $V_{CE(SAT)}$

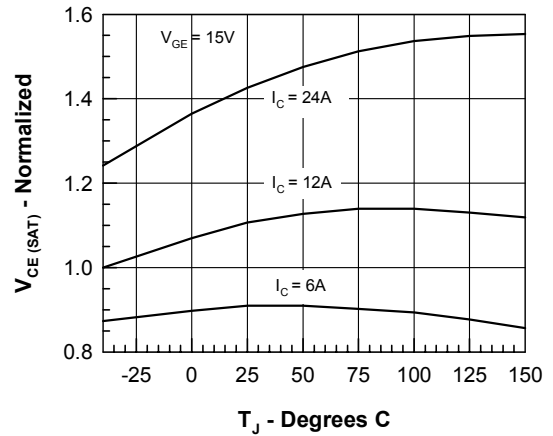


Fig. 5. Admittance Curves

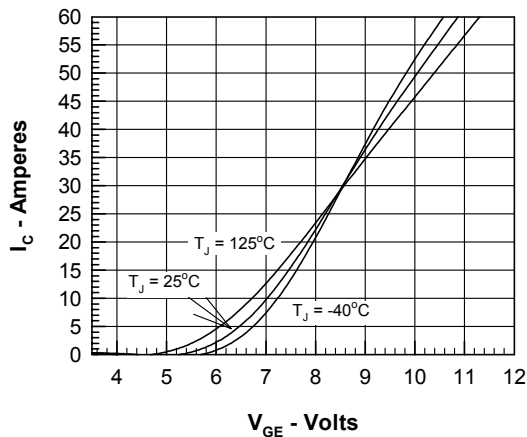


Fig. 6. Capacitance Curves

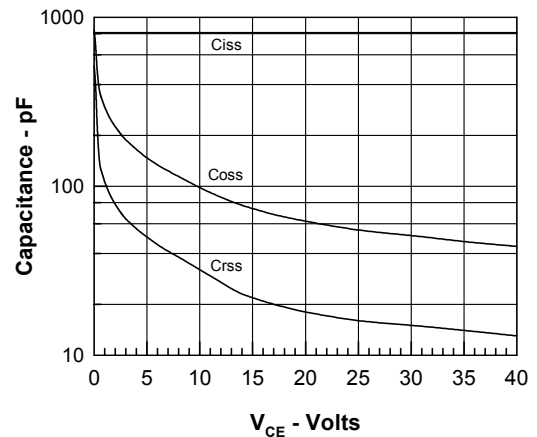


Fig. 7. Dependence of E_{OFF} on I_C

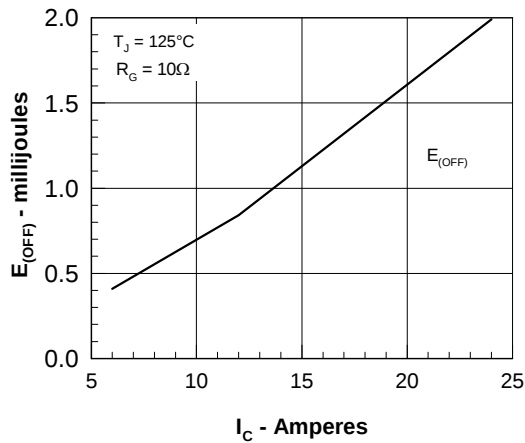


Fig. 8. Dependence of E_{OFF} on R_G

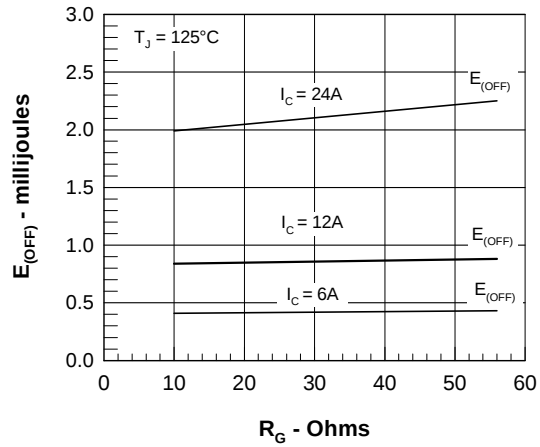


Fig. 9. Gate Charge

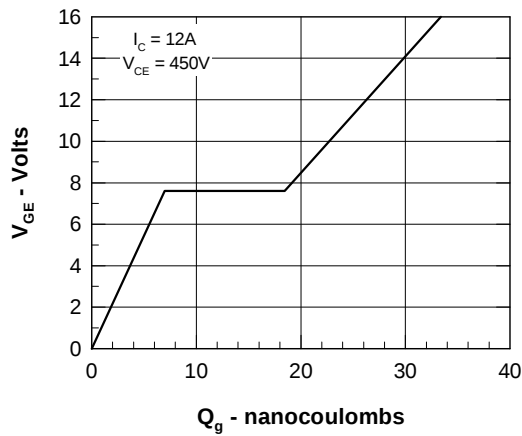


Fig. 10. Turn-off Safe Operating Area

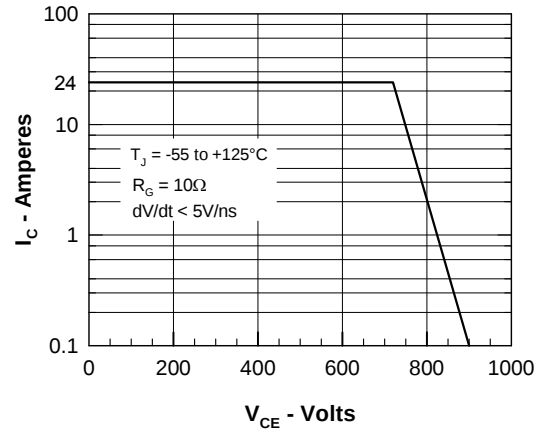


Fig. 11. Transient Thermal Resistance

